

Low-Voltage CMOS Quad 2-Input Multiplexer

MC74LCX257

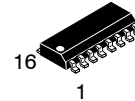
With 5.0 V–Tolerant Inputs and Outputs
(3–State, Non–Inverting)

The MC74LCX257 is a high performance, quad 2–input multiplexer with 3–state outputs operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5 V allows MC74LCX257 inputs to be safely driven from 5.0 V devices.

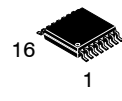
Four bits of data from two sources can be selected using the Select input. The four outputs present the selected data in the true (non–inverted) form. The outputs may be switched to a high impedance state by placing a logic HIGH on the Output Enable ($\overline{OE}$) input. Current drive capability is 24 mA at the outputs.

Features

- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5.0 V Tolerant – Interface Capability with 5.0 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0$ V
- LVTTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μ A) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance:
 - ◆ Human Body Model >2000 V
 - ◆ Machine Model >200 V
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

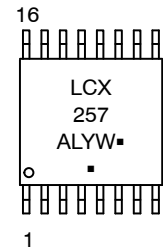
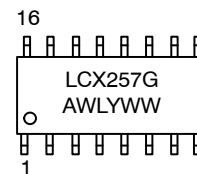


SOIC–16
D SUFFIX
CASE 751B



TSSOP–16
DT SUFFIX
CASE 948F

MARKING DIAGRAM



A = Assembly Location
 WL, L = Wafer Lot
 Y = Year
 WW, W = Work Week
 G or ■ = Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

MC74LCX257

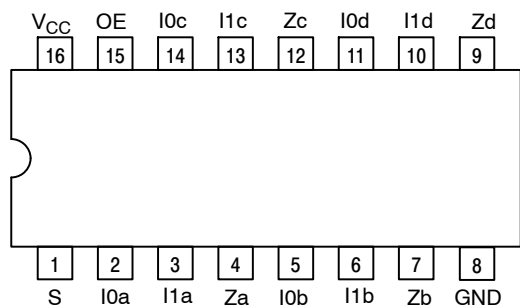


Figure 1. Pinout: 16-Lead Plastic Package
(Top View)

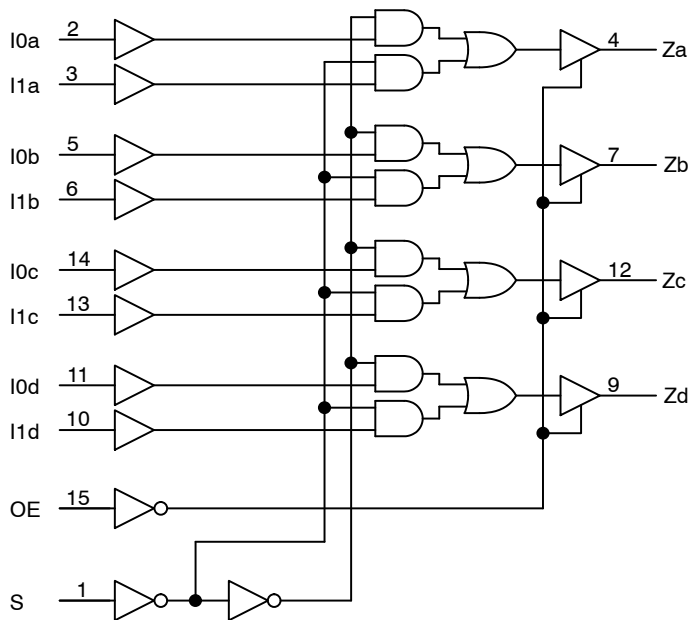


Figure 2. Logic Diagram

PIN NAMES

Pins	Function
I0n	Source 0 Data Inputs
I1n	Source 1 Data Inputs
$\overline{OE}$	Output Enable Input
S	Select Input
Zn	Outputs

TRUTH TABLE

Inputs				Outputs
$\overline{OE}$	S	I0n	I1n	Zn
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L	L	X	L
L	L	H	X	H

H = High Voltage Level
L = Low Voltage Level
X = High or Low Voltage Level and Transitions are Acceptable
Z = High Impedance State

For ICC reasons, DO NOT FLOAT Inputs

MC74LCX257

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Units
V_{CC}	DC Supply Voltage	-0.5 to +7.0		V
V_I	DC Input Voltage	$-0.5 \leq V_I \leq +7.0$		V
V_O	DC Output Voltage	$-0.5 \leq V_I \leq +7.0$	Output in 3-State	V
		$-0.5 \leq V_O \leq V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1)	V
I_{IK}	DC Input Diode Current	-50	$V_I < GND$	mA
I_{OK}	DC Output Diode Current	-50	$V_O < GND$	mA
		+50	$V_O > V_{CC}$	mA
I_O	DC Output Source/Sink Current	± 50		mA
I_{CC}	DC Supply Current Per Supply Pin	± 100		mA
I_{GND}	DC Ground Current Per Ground Pin	± 100		mA
T_{STG}	Storage Temperature Range	-65 to +150		°C
MSL	Moisture Sensitivity		Level 1	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Type	Max	Units
V_{CC}	Supply Voltage Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	3.6 3.6	V
V_I	Input Voltage	0		5.5	V
V_O	Output Voltage (HIGH or LOW State) (3-State)	0 0		V_{CC} 5.5	V
I_{OH}	HIGH Level Output Current $V_{CC} = 3.0\text{ V} - 3.6\text{ V}$ $V_{CC} = 2.7\text{ V} - 3.0\text{ V}$ $V_{CC} = 2.3\text{ V} - 2.7\text{ V}$			-24 -12 -8	mA
I_{OL}	LOW Level Output Current $V_{CC} = 3.0\text{ V} - 3.6\text{ V}$ $V_{CC} = 2.7\text{ V} - 3.0\text{ V}$ $V_{CC} = 2.3\text{ V} - 2.7\text{ V}$			+24 +12 +8	mA
T_A	Operating Free-Air Temperature	-40		+85	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, V_{IN} from 0.8 V to 2.0 V, $V_{CC} = 3.0\text{ V}$	0		10	ns/V

ORDERING INFORMATION

Device	Package	Shipping†
MC74LCX257DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74LCX257DTG	TSSOP-16 (Pb-Free)	96 Units / Rail
MC74LCX257DTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

MC74LCX257

DC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic	Condition	T _A = -40°C to +85°C		Units
			Min	Max	
V _{IH}	HIGH Level Input Voltage (Note 2)	2.3 V ≤ V _{CC} ≤ 2.7 V	1.7		V
		2.7 V ≤ V _{CC} ≤ 3.6 V	2.0		
V _{IL}	LOW Level Input Voltage (Note 2)	2.3 V ≤ V _{CC} ≤ 2.7 V		0.7	V
		2.7 V ≤ V _{CC} ≤ 3.6 V		0.8	
V _{OH}	HIGH Level Output Voltage	2.3 V ≤ V _{CC} ≤ 3.6 V; I _{OH} = -100 μA	V _{CC} - 0.2		V
		V _{CC} = 2.3 V; I _{OH} = -8 mA	1.8		
		V _{CC} = 2.7 V; I _{OH} = -12 mA	2.2		
		V _{CC} = 3.0 V; I _{OH} = -18 mA	2.4		
		V _{CC} = 3.0 V; I _{OH} = -24 mA	2.2		
V _{OL}	LOW Level Output Voltage	2.3 V ≤ V _{CC} ≤ 3.6 V; I _{OL} = 100 μA		0.2	V
		V _{CC} = 2.3 V; I _{OL} = 8 mA		0.6	
		V _{CC} = 2.7 V; I _{OL} = 12 mA		0.4	
		V _{CC} = 3.0 V; I _{OL} = 16 mA		0.4	
		V _{CC} = 3.0 V; I _{OL} = 24 mA		0.55	
I _{OZ}	3-State Output Current	V _{CC} = 3.6 V, V _{IN} = V _{IH} or V _{IL} , V _{OUT} = 0 to 5.5 V		±5	μA
I _{OFF}	Power Off Leakage Current	V _{CC} = 0, V _{IN} = 5.5 V or V _{OUT} = 5.5 V		10	μA
I _{IN}	Input Leakage Current	V _{CC} = 3.6 V, V _{IN} = 5.5 V or GND		±5	μA
I _{CC}	Quiescent Supply Current	V _{CC} = 3.6 V, V _{IN} = 5.5 V or GND		10	μA
ΔI _{CC}	Increase in I _{CC} per Input	2.3 ≤ V _{CC} ≤ 3.6 V; V _{IH} = V _{CC} - 0.6 V		500	μA

2. These values of V_I are used to test DC electrical characteristics only.

AC CHARACTERISTICS t_{RI} = t_{FI} = 2.5 ns; R_L = 500 Ω

Symbol	Parameter	Waveform	Limits						Units
			T _A = -40°C to +85°C						
			V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 2.7 V		V _{CC} = 2.5 V ± 0.2 V		
			C _L = 50 pF		C _L = 50 pF		C _L = 30 pF		
			Min	Max	Min	Max	Min	Max	
t _{PLH} t _{PHL}	Propagation Delay In to Zn	1	1.5 1.5	6.0 6.0	1.5 1.5	6.5 6.5	1.5 1.5	7.2 7.2	ns
t _{PLH} t _{PHL}	Propagation Delay S to Zn	1, 2	1.5 1.5	7.0 7.0	1.5 1.5	8.5 8.5	1.5 1.5	9.1 9.1	ns
t _{PZH} t _{PZL}	Output Enable Time to High and Low Level	3	1.5 1.5	7.0 7.0	1.5 1.5	8.5 8.5	1.5 1.5	9.1 9.1	ns
t _{PHZ} t _{PLZ}	Output Disable Time from High and Low Level	3	1.5 1.5	5.5 5.5	1.5 1.5	6.0 6.0	1.5 1.5	6.6 6.6	ns
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 3)			1.0 1.0					ns

3. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

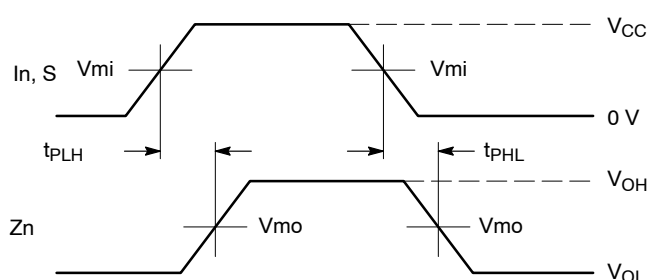
DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Characteristic	Condition	$T_A = +25^\circ\text{C}$			Units
			Min	Typ	Max	
V_{OLP}	Dynamic LOW Peak Voltage (Note 4)	$V_{CC} = 3.3\text{ V}, C_L = 50\text{ pF}, V_{IH} = 3.3\text{ V}, V_{IL} = 0\text{ V}$ $V_{CC} = 2.5\text{ V}, C_L = 30\text{ pF}, V_{IH} = 2.5\text{ V}, V_{IL} = 0\text{ V}$		0.8 0.6		V
V_{OLV}	Dynamic LOW Valley Voltage (Note 4)	$V_{CC} = 3.3\text{ V}, C_L = 50\text{ pF}, V_{IH} = 3.3\text{ V}, V_{IL} = 0\text{ V}$ $V_{CC} = 2.5\text{ V}, C_L = 30\text{ pF}, V_{IH} = 2.5\text{ V}, V_{IL} = 0\text{ V}$		-0.8 -0.6		V

4. Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

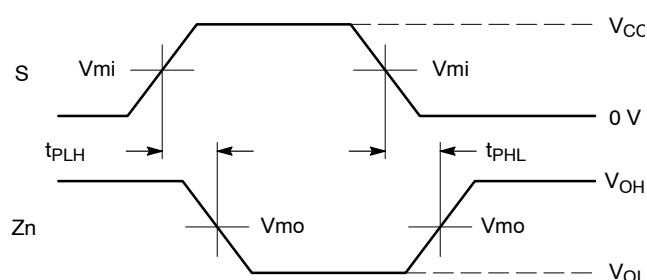
CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C_{IN}	Input Capacitance	$V_{CC} = 3.3\text{ V}, V_I = 0\text{ V or } V_{CC}$	7	pF
$C_{I/O}$	Input/Output Capacitance	$V_{CC} = 3.3\text{ V}, V_I = 0\text{ V or } V_{CC}$	8	pF
C_{PD}	Power Dissipation Capacitance	10 MHz, $V_{CC} = 3.3\text{ V}, V_I = 0\text{ V or } V_{CC}$	25	pF



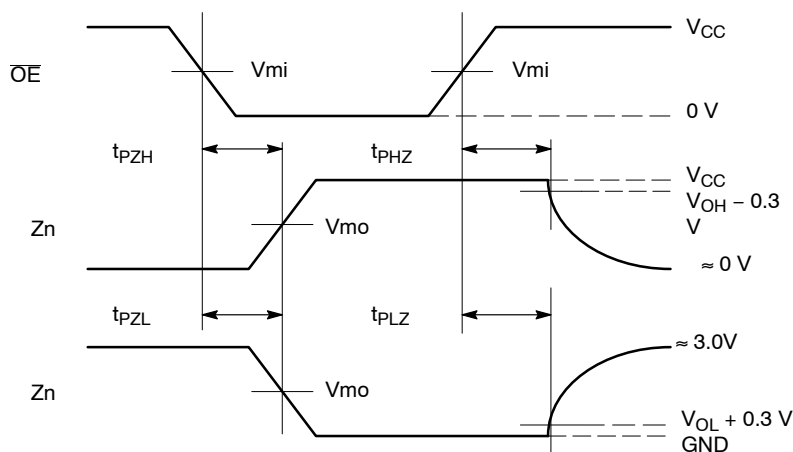
WAVEFORM 1 – NON-INVERTING PROPAGATION DELAYS

$t_R = t_F = 2.5\text{ ns}$, 10% to 90%; $f = 1.0\text{ MHz}$; $t_W = 500\text{ ns}$



WAVEFORM 2 – INVERTING PROPAGATION DELAYS

$t_R = t_F = 2.5\text{ ns}$, 10% to 90%; $f = 1.0\text{ MHz}$; $t_W = 500\text{ ns}$

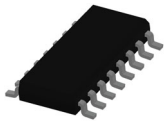


WAVEFORM 3 – OUTPUT ENABLE AND DISABLE TIMES

$t_R = t_F = 2.5\text{ ns}$, 10% to 90%; $f = 1.0\text{ MHz}$; $t_W = 500\text{ ns}$

Symbol	V_{CC}		
	$3.3\text{ V} \pm 0.3\text{ V}$	2.7 V	$2.5\text{ V} \pm 0.2\text{ V}$
V_{mi}	1.5 V	1.5 V	$V_{CC}/2$
V_{mo}	1.5 V	1.5 V	$V_{CC}/2$
V_{HZ}	$V_{OL} + 0.3\text{ V}$	$V_{OL} + 0.3\text{ V}$	$V_{OL} + 0.15\text{ V}$
V_{LZ}	$V_{OH} - 0.3\text{ V}$	$V_{OH} - 0.3\text{ V}$	$V_{OH} - 0.15\text{ V}$

Figure 3. AC Waveforms

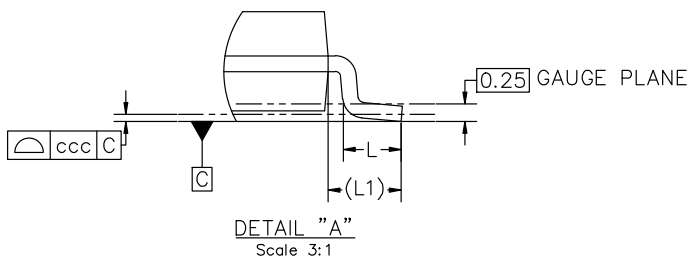
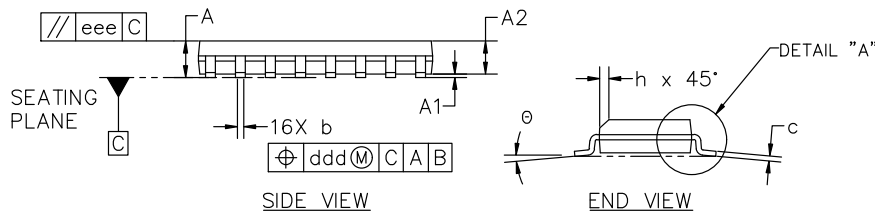
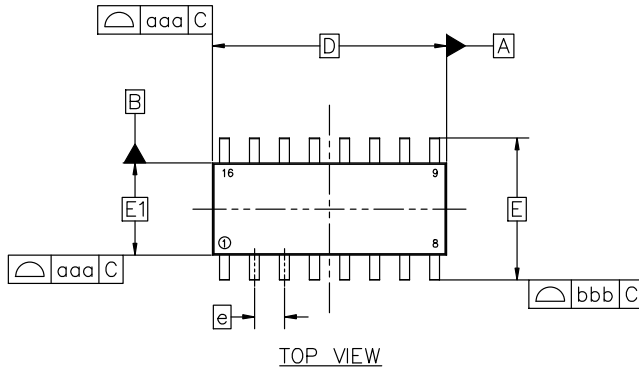


SOIC-16 9.90x3.90x1.37 1.27P
CASE 751B
ISSUE M

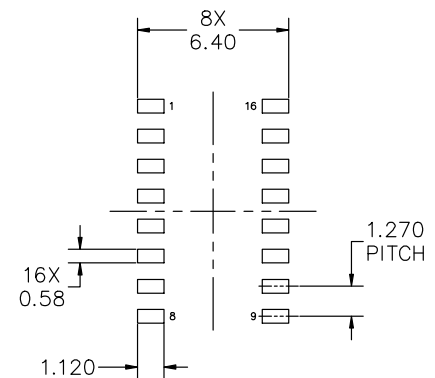
DATE 18 OCT 2024

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
5. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE b DIMENSION AT MAXIMUM MATERIAL CONDITION.



MILLIMETERS			
DIM	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.10	0.18	0.25
A2	1.25	1.37	1.50
b	0.35	0.42	0.49
c	0.19	0.22	0.25
D	9.90 BSC		
E	6.00 BSC		
E1	3.90 BSC		
e	1.27 BSC		
h	0.25	---	0.50
L	0.40	0.83	1.25
L1	1.05 REF		
θ	0°	---	7°
TOLERANCE OF FORM AND POSITION			
aaa	0.10		
bbb	0.20		
ccc	0.10		
ddd	0.25		
eee	0.10		



*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE onsemi SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D

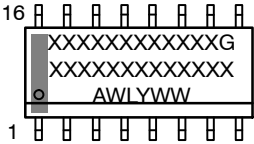
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DESCRIPTION:	SOIC-16 9.90X3.90X1.37 1.27P	PAGE 1 OF 2

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SOIC-16 9.90x3.90x1.37 1.27P
CASE 751B
ISSUE M

DATE 18 OCT 2024

GENERIC
MARKING DIAGRAM*



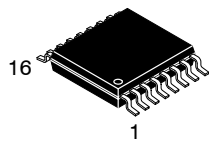
XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

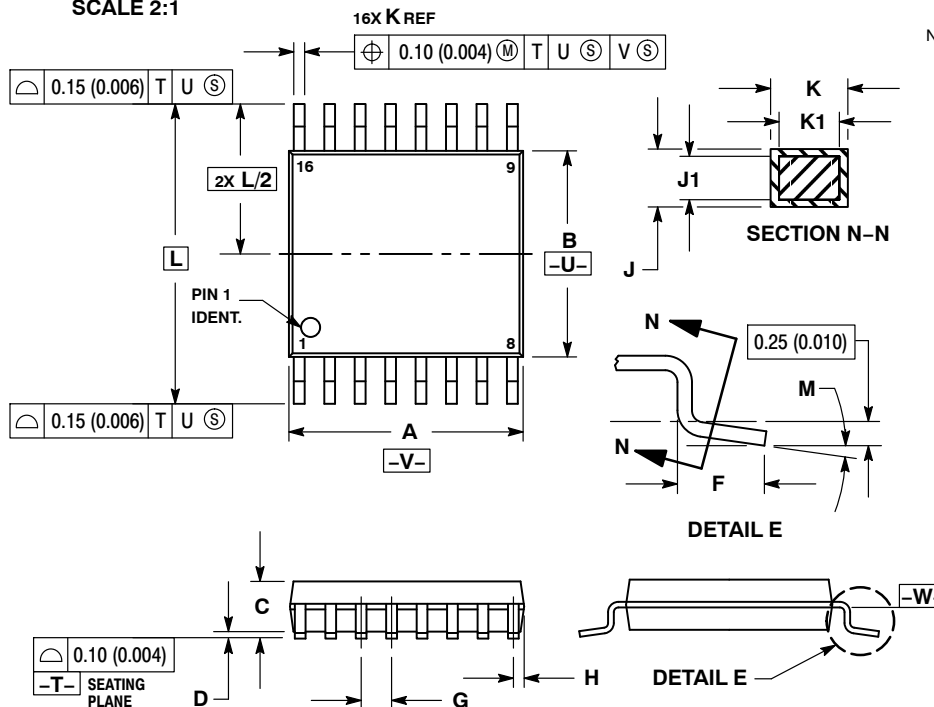
STYLE 1: PIN 1. COLLECTOR 2. BASE 3. EMITTER 4. NO CONNECTION 5. EMITTER 6. BASE 7. COLLECTOR 8. COLLECTOR 9. BASE 10. EMITTER 11. NO CONNECTION 12. EMITTER 13. BASE 14. COLLECTOR 15. EMITTER 16. COLLECTOR	STYLE 2: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION 4. CATHODE 5. CATHODE 6. NO CONNECTION 7. ANODE 8. CATHODE 9. CATHODE 10. ANODE 11. NO CONNECTION 12. CATHODE 13. CATHODE 14. NO CONNECTION 15. ANODE 16. CATHODE	STYLE 3: PIN 1. COLLECTOR, DYE #1 2. BASE, #1 3. EMITTER, #1 4. COLLECTOR, #1 5. COLLECTOR, #2 6. BASE, #2 7. EMITTER, #2 8. COLLECTOR, #2 9. COLLECTOR, #3 10. BASE, #3 11. EMITTER, #3 12. COLLECTOR, #3 13. COLLECTOR, #4 14. BASE, #4 15. EMITTER, #4 16. COLLECTOR, #4	STYLE 4: PIN 1. COLLECTOR, DYE #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. COLLECTOR, #3 6. COLLECTOR, #3 7. COLLECTOR, #4 8. COLLECTOR, #4 9. BASE, #4 10. EMITTER, #4 11. BASE, #3 12. EMITTER, #3 13. BASE, #2 14. EMITTER, #2 15. BASE, #1 16. EMITTER, #1
STYLE 5: PIN 1. DRAIN, DYE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. DRAIN, #3 6. DRAIN, #3 7. DRAIN, #4 8. DRAIN, #4 9. GATE, #4 10. SOURCE, #4 11. GATE, #3 12. SOURCE, #3 13. GATE, #2 14. SOURCE, #2 15. GATE, #1 16. SOURCE, #1	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. CATHODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE 15. ANODE 16. ANODE	STYLE 7: PIN 1. SOURCE N-CH 2. COMMON DRAIN (OUTPUT) 3. COMMON DRAIN (OUTPUT) 4. GATE P-CH 5. COMMON DRAIN (OUTPUT) 6. COMMON DRAIN (OUTPUT) 7. COMMON DRAIN (OUTPUT) 8. SOURCE P-CH 9. SOURCE P-CH 10. COMMON DRAIN (OUTPUT) 11. COMMON DRAIN (OUTPUT) 12. COMMON DRAIN (OUTPUT) 13. GATE N-CH 14. COMMON DRAIN (OUTPUT) 15. COMMON DRAIN (OUTPUT) 16. SOURCE N-CH	

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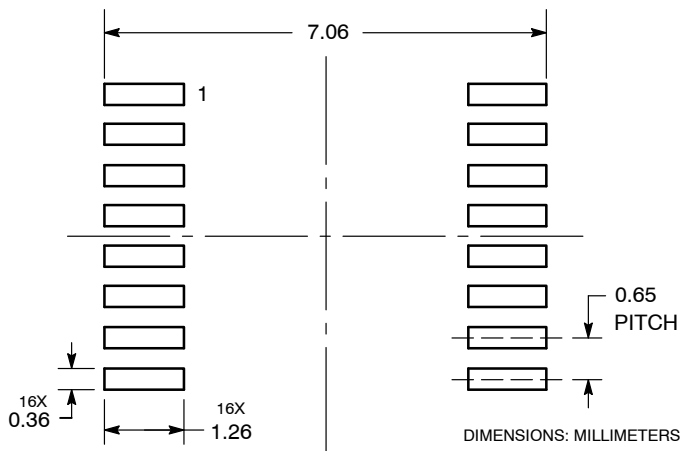

TSSOP-16 WB
CASE 948F
ISSUE B

DATE 19 OCT 2006

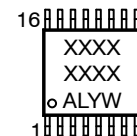

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

**RECOMMENDED
SOLDERING FOOTPRINT***


*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**GENERIC
MARKING DIAGRAM***


XXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
G or ■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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